

ABSTRACT

The object of this invention is to provide an organometallic precursor for forming a metal film or pattern and a method of forming the metal film or pattern using the same. More particularly, the present invention provides an organometallic precursor containing a hydrazine-based compound coordinated with a central metal thereof, and a method of forming a metal film or pattern using the same. Further, the present invention provides a composition containing an organometallic compound and a hydrazine-based compound, and a method of forming a metal film or pattern using the same. Additionally, the present invention is advantageous in that a pure metal film or pattern is formed using the organometallic precursor or composition through a simple procedure without limiting atmospheric conditions at a low temperature, and the film or pattern thus formed has excellent conductivity and morphology. Therefore, the film is useful in an electronic device field including flexible displays and large-sized TFT-LCD.